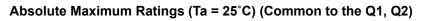
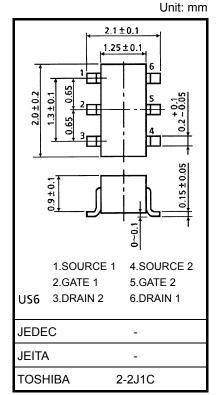
TOSHIBA Field-Effect Transistor Silicon P-Channel MOS Type

# SSM6P35FU

- High-Speed Switching Applications
- Analog Switch Applications
- 1.2-V drive
- Low ON-resistance :  $R_{on}$  = 44  $\Omega$  (max) (@V<sub>GS</sub> = -1.2 V)
  - :  $R_{on} = 22 \Omega (max) (@V_{GS} = -1.5 V)$
  - : R<sub>on</sub> = 11  $\Omega$  (max) (@V<sub>GS</sub> = -2.5 V)
  - :  $R_{on} = 8 \Omega (max) (@V_{GS} = -4.0 V)$



Characteristics	Symbol	Rating	Unit		
Drain-source voltage	V <sub>DSS</sub>	-20	V		
Gate-source voltage		V <sub>GSS</sub>	±10	V	
Drain current	DC	۱ <sub>D</sub>	-100	mA	
	Pulse	IDP	-200	ША	
Drain power dissipation	P <sub>D</sub> (Note 1)	200	mW		
Channel temperature		T <sub>ch</sub>	150	°C	
Storage temperature		T <sub>stg</sub>	–55 to 150	°C	



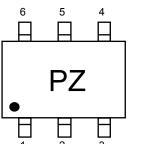
Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in

Weight: 6.8 mg (typ.)

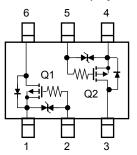
temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Total rating

#### Marking



#### Equivalent Circuit (top view)



Start of commercial production 2008-03

#### Electrical Characteristics (Ta = 25°C) (Common to the Q1, Q2)

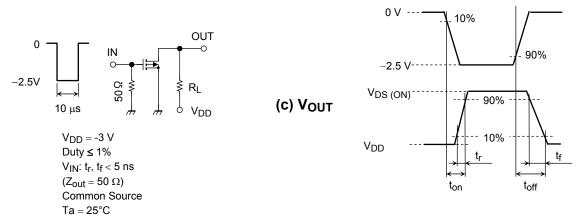
Charac	teristics	Symbol	Test Condition		Min	Тур.	Max	Unit
Gate leakage curre	ent	I <sub>GSS</sub>	$V_{GS}=\pm 10~V,~V_{DS}=0~V$				±10	μA
Drain-source brea	kdown voltage	V (BR) DSS	$I_D = -0.1 \text{ mA}, V_{GS} = 0 \text{ V}$		-20	_	_	V
Drain cutoff curren	t	I <sub>DSS</sub>	$V_{DS} = -20 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$		_	_	-1	μA
Gate threshold volt	tage	V <sub>th</sub>	$V_{DS} = -3 V, I_D = -1 mA$		-0.4	_	-1.0	V
Forward transfer a	dmittance	Y <sub>fs</sub>	$V_{DS} = -3 V, I_D = -50 mA$	(Note 2)	77			mS
		R <sub>DS</sub> (ON)	$I_{D} = -50 \text{ mA}, \text{ V}_{GS} = -4 \text{ V}$	(Note 2)	_	4.3	8	Ω
Drain-source ON-resistance	$I_D = -50 \text{ mA}, \text{ V}_{GS} = -2.5 \text{ V}$		(Note 2)	_	5.6	11		
	I <sub>D</sub> = -5 mA, V <sub>GS</sub> = -1.5 V		(Note 2)		8.2	22		
			$I_D = -2 \text{ mA}, V_{GS} = -1.2 \text{ V}$	(Note 2)		11	44	
Input capacitance Reverse transfer capacitance		C <sub>iss</sub>	V <sub>DS</sub> = -3 V, V <sub>GS</sub> = 0 V, f = 1 MHz			12.2		pF
		C <sub>rss</sub>				6.5		
Output capacitance	e	C <sub>oss</sub>				10.4		
Switching time	Turn-on time	t <sub>on</sub>	$V_{DD} = -3 \text{ V}, \text{ I}_{D} = -50 \text{ mA},$ $V_{GS} = 0 \text{ to } -2.5 \text{ V}$		_	175	_	
	Turn-off time	t <sub>off</sub>			_	251	_	ns
Drain-source forward voltage		V <sub>DSF</sub>	$I_D = 100 \text{ mA}, V_{GS} = 0 \text{ V}$	(Note 2)	_	0.83	1.2	V

Note 2: Pulse test

#### Switching Time Test Circuit (Common to the Q1, Q2)

(a) Test Circuit

(b) V<sub>IN</sub>



#### Notice on Usage

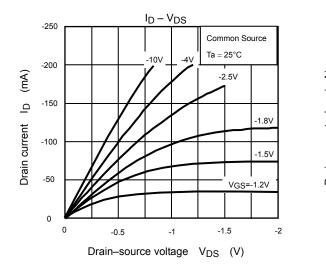
Let V<sub>th</sub> be the voltage applied between gate and source that causes the drain current (I<sub>D</sub>) to below (–1 mA for the SSM6P35FU). Then, for normal switching operation, V<sub>GS(on)</sub> must be higher than V<sub>th</sub>, and V<sub>GS(off)</sub> must be lower than V<sub>th</sub>. This relationship can be expressed as: V<sub>GS(off)</sub> < V<sub>th</sub> < V<sub>GS(on)</sub>.

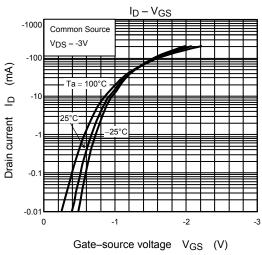
Take this into consideration when using the device.

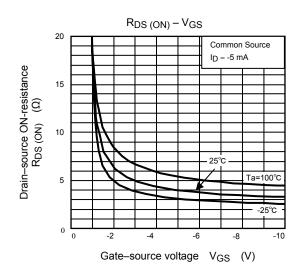
#### **Handling Precaution**

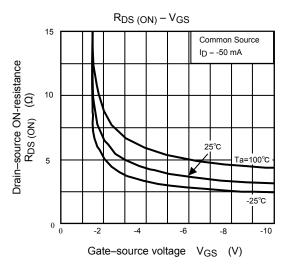
When handling individual devices that are not yet mounted on a circuit board, make sure that the environment is protected against electrostatic discharge. Operators should wear antistatic clothing, and containers and other objects that come into direct contact with devices should be made of antistatic materials.

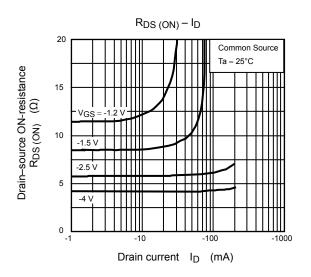
## **TOSHIBA**











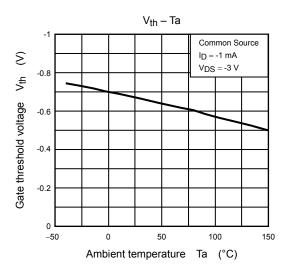
R<sub>DS (ON)</sub> – Ta 20 Common Source VGS -1.2 V, ID=-2mA 15 -5mA 1.5 V, 10 2.5 V, -50mA 4V. -50mA 5 0 -50 0 50 100

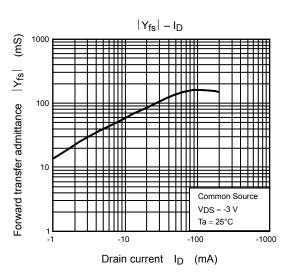
Ambient temperature Ta (°C)

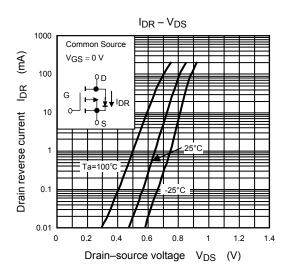
150

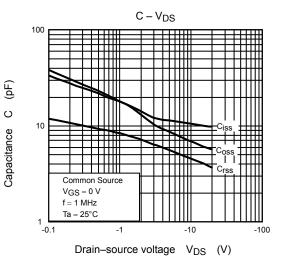
Drain–source ON-resistance  $R_{DS}(ON)$  ( $\Omega$ )

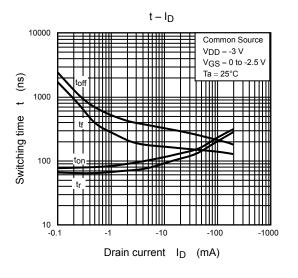
## **TOSHIBA**

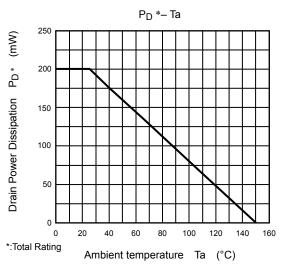












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